MJE18006G

SWITCHMODE ™

NPN Bipolar Power Transistor
For Switching Power Supply Applications

The MJE18006G has an applications specific state−of−the−art die designed for use in 220 V line−operated SWITCHMODE Power supplies and electronic light ballasts.

Features

- Improved Efficiency Due to Low Base Drive Requirements:
  - High and Flat DC Current Gain h_{FE}
  - Fast Switching
  - No Coil Required in Base Circuit for Turn−Off (No Current Tail)
- Tight Parametric Distributions are Consistent Lot−to−Lot
- Standard TO−220
- These Devices are Pb−Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Sustaining Voltage	V_{CEO}	450	Vdc
Collector−Emitter Breakdown Voltage	V_{CES}	1000	Vdc
Emitter−Base Voltage	V_{EBO}	9.0	Vdc
Collector Current − Continuous − Peak (Note 1)	I_C I_{CM}	6.0 15	Adc
Base Current − Continuous − Peak (Note 1)	I_B I_{BM}	4.0 8.0	Adc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	100 0.8	W W/°C
Operating and Storage Temperature	T_J, T_{stg}	−65 to 150	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	1.25	°C/W
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8″ from Case for 5 Seconds	T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.
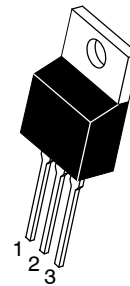1. Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%.

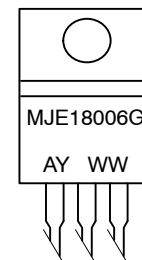*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

POWER TRANSISTOR
6.0 AMPERES
1000 VOLTS – 100 WATTS

TO−220AB
CASE 221A−09
STYLE 1

MARKING DIAGRAM

MJE18006G

AY WW

A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJE18006G	TO−220 (Pb−Free)	50 Units / Rail

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise specified)

Characteristic				Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS								
Collector–Emitter Sustaining Voltage (I_C = 100 mA, L = 25 mH)				$V_{CEO(sus)}$	450	–	–	Vdc
Collector Cutoff Current (V_{CE} = Rated V_{CEO}, I_B = 0)				I_{CEO}	–	–	100	µAdc
Collector Cutoff Current (V_{CE} = Rated V_{CES}, V_{EB} = 0)			(T_C = 125°C)	I_{CES}	– –	– –	100 500	µAdc
(V_{CE} = 800 V, V_{EB} = 0)			(T_C = 125°C)		–	–	100	
Emitter Cutoff Current (V_{EB} = 9.0 Vdc, I_C = 0)				I_{EBO}	–	–	100	µAdc
ON CHARACTERISTICS								
Base–Emitter Saturation Voltage (I_C = 1.3 Adc, I_B = 0.13 Adc) (I_C = 3.0 Adc, I_B = 0.6 Adc)				$V_{BE(sat)}$	– –	0.83 0.94	1.2 1.3	Vdc

Collector–Emitter Saturation Voltage
  (I_C = 1.3 Adc, I_B = 0.13 Adc)
 	
  (I_C = 3.0 Adc, I_B = 0.6 Adc)
		(T_C = 125°C)
		
		(T_C = 125°C)
				$V_{CE(sat)}$	–
					–
					–
					–
						0.25
						0.27
						0.35
						0.4
							0.6
							0.65
							0.7
							0.8
								Vdc

DC Current Gain (I_C = 0.5 Adc, V_{CE} = 5.0 Vdc)
 	
  (I_C = 3.0 Adc, V_{CE} = 1.0 Vdc)
 	
  (I_C = 1.3 Adc, V_{CE} = 1.0 Vdc)
  (I_C = 10 mAdc, V_{CE} = 5.0 Vdc)
		(T_C = 125°C)
		
		(T_C = 125°C)
		(T_C = 25 to 125°C)
				h_{FE}	14
					–
					6.0
					5.0
					11
					10
						–
						32
						10
						8.0
						17
						22
							34
							–
							–
							–
							–
							–
								–

DYNAMIC CHARACTERISTICS								
Current Gain Bandwidth (I_C = 0.5 Adc, V_{CE} = 10 Vdc, f = 1.0 MHz)				f_T	–	14	–	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)				C_{ob}	–	75	120	pF
Input Capacitance (V_{EB} = 8.0 V)				C_{ib}	–	1000	1500	pF

Dynamic Saturation Voltage:
 	
  Determined 1.0 µs and 3.0 µs respectively after rising I_{B1} reaches 90% of final I_{B1}
  (see Figure 18)
	(I_C = 1.3 Adc
	I_{B1} = 130 mAdc
	V_{CC} = 300 V)
		1.0 µs	(T_C = 125°C)	$V_{CE(dsat)}$	–
					–
						5.5
						12
							–
							–
								V

		3.0 µs	(T_C = 125°C)		– –	3.0 7.0	– –	
	(I_C = 3.0 Adc I_{B1} = 0.6 Adc V_{CC} = 300 V)	1.0 µs	(T_C = 125°C)		– –	9.5 14.5	– –	
		3.0 µs	(T_C = 125°C)		– –	2.0 7.5	– –	
SWITCHING CHARACTERISTICS: Resistive Load (D.C. ≤ 10%, Pulse Width = 20 µs)								
Turn–On Time	(I_C = 3.0 Adc, I_{B1} = 0.6 Adc, I_{B2} = 1.5 Adc, V_{CC} = 300 V)		(T_C = 125°C)	t_{on}	– –	90 100	180 –	ns
Turn–Off Time			(T_C = 125°C)	t_{off}	– –	1.7 2.1	2.5 –	µs
Turn–On Time	(I_C = 1.3 Adc, I_{B1} = 0.13 Adc, I_{B2} = 0.65 Adc, V_{CC} = 300 V)		(T_C = 125°C)	t_{on}	– –	200 130	300 –	ns
Turn–Off Time			(T_C = 125°C)	t_{off}	– –	1.2 1.5	2.5 –	µs
SWITCHING CHARACTERISTICS: Inductive Load (V_{clamp} = 300 V, V_{CC} = 15 V, L = 200 µH)								
Fall Time	(I_C = 1.5 Adc, I_{B1} = 0.13 Adc, I_{B2} = 0.65 Adc)		(T_C = 125°C)	t_{fi}	– –	100 120	180 –	ns
Storage Time			(T_C = 125°C)	t_{si}	– –	1.5 1.9	2.5 –	µs
Crossover Time			(T_C = 125°C)	t_c	– –	220 230	350 –	ns
Fall Time	(I_C = 3.0 Adc, I_{B1} = 0.6 Adc, I_{B2} = 1.5 Adc)		(T_C = 125°C)	t_{fi}	– –	85 120	150 –	ns
Storage Time			(T_C = 125°C)	t_{si}	– –	2.15 2.75	3.2 –	µs
Crossover Time			(T_C = 125°C)	t_c	– –	200 310	300 –	ns

2. Proper strike and creepage distance must be provided.
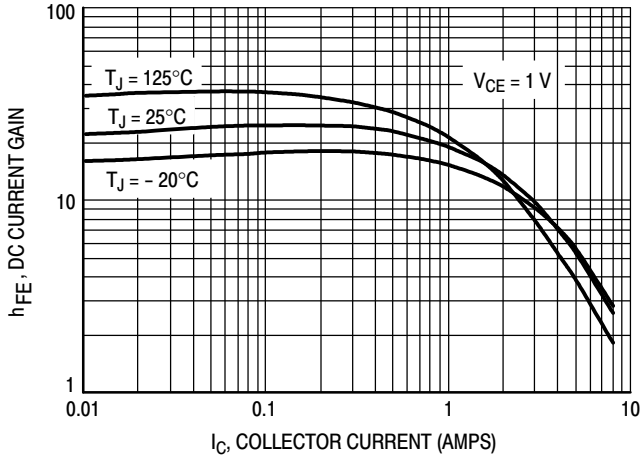
MJE18006G

TYPICAL STATIC CHARACTERISTICS

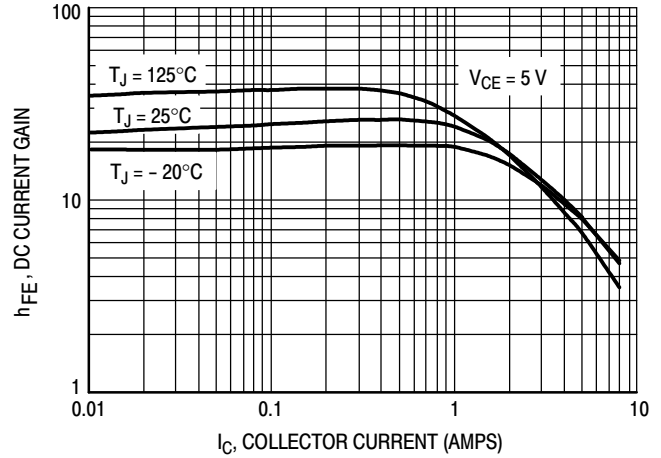**Figure 1. DC Current Gain @ 1 Volt**
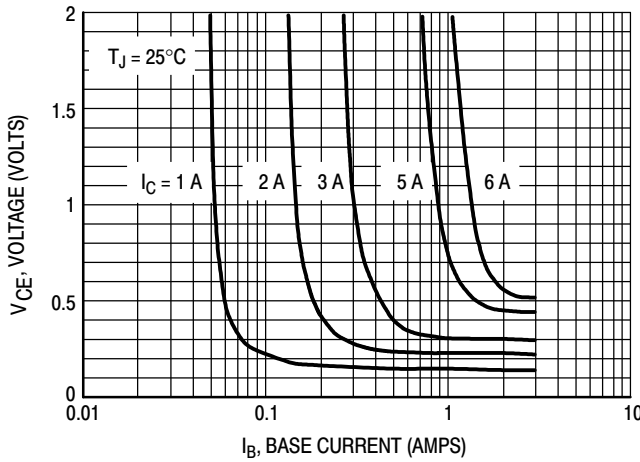

Figure 2. DC Current Gain @ 5 Volts

Figure 3. Collector Saturation Region
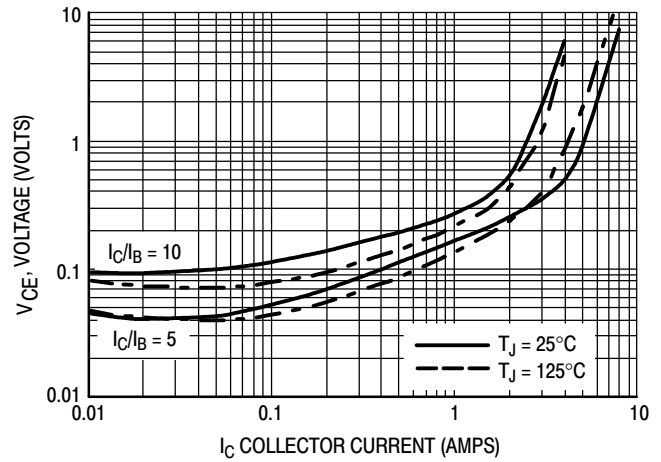
Figure 4. Collector−Emitter Saturation Voltage

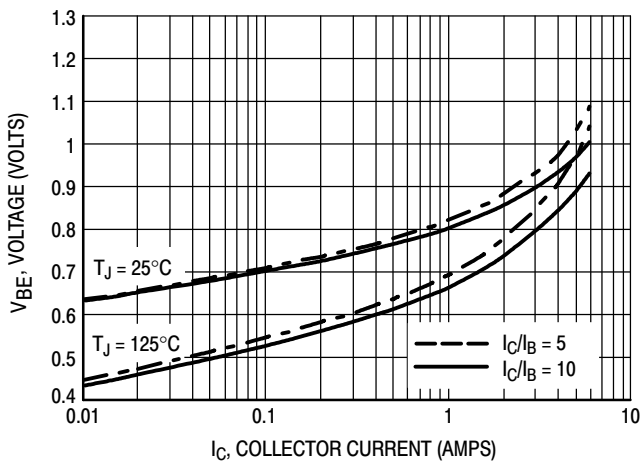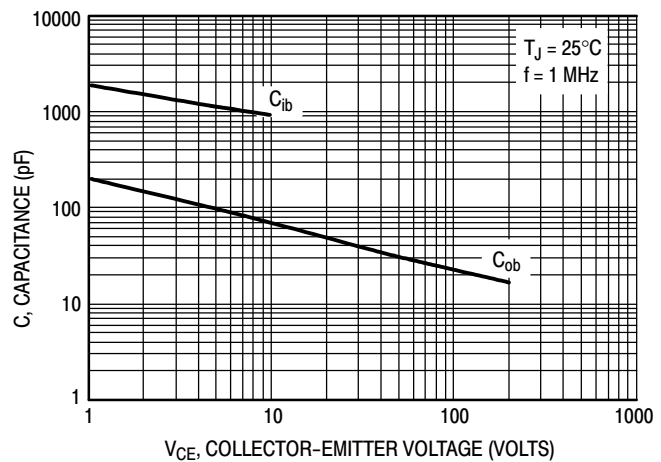**Figure 5. Base−Emitter Saturation Region**

Figure 6. Capacitance

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TYPICAL SWITCHING CHARACTERISTICS
($I_{B2} = I_C/2$ for all switching)
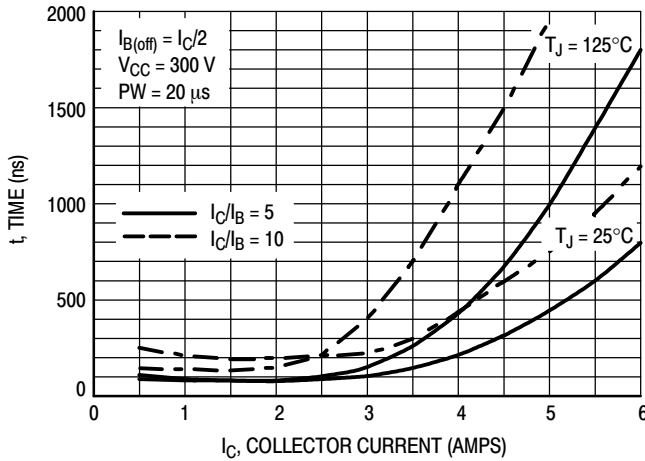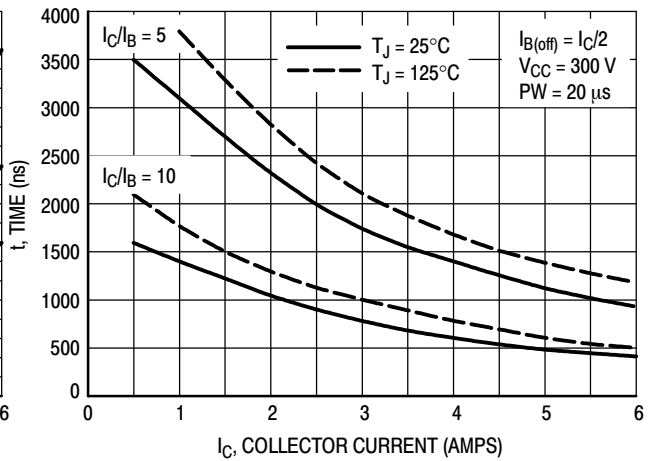

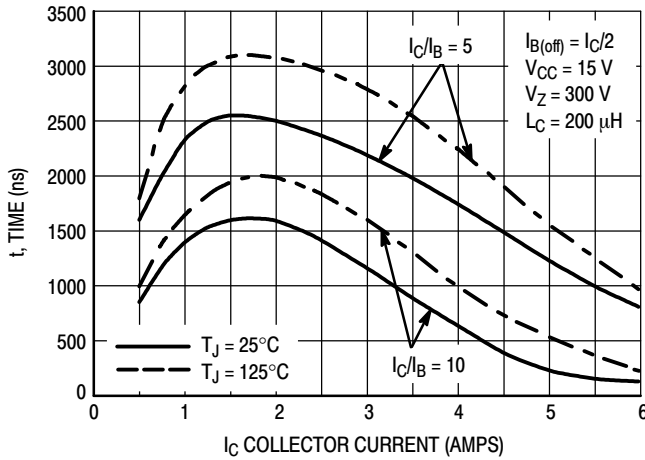Figure 7. Resistive Switching, t_{on}

Figure 8. Resistive Switching, t_{off}

Figure 9. Inductive Storage Time, t_{si}
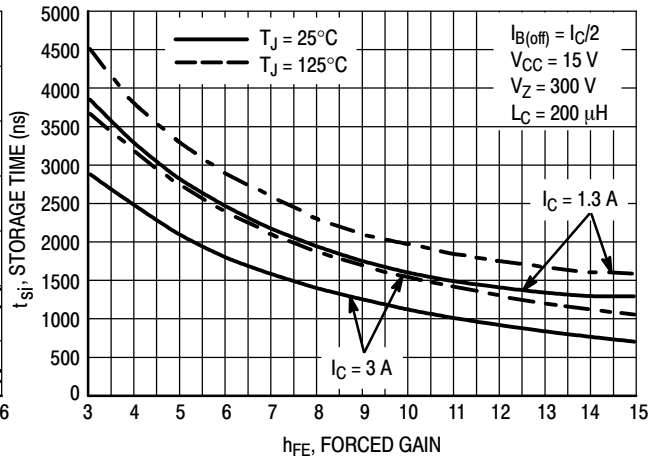
Figure 10. Inductive Storage Time, $t_{si}(h_{FE})$
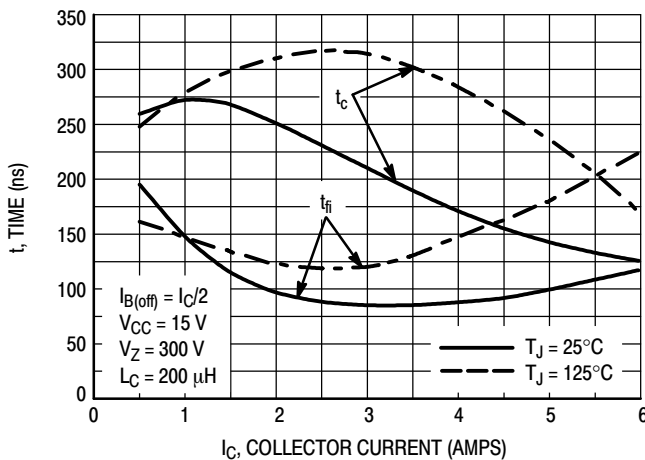
Figure 11. Inductive Switching, t_c and t_{fi}
$I_C/I_B = 5$
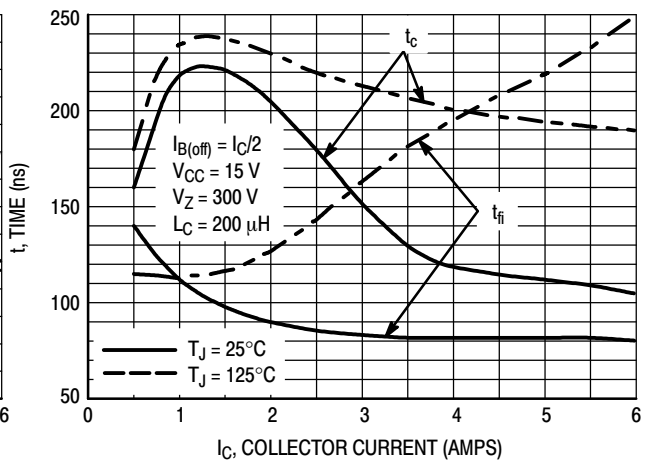
Figure 12. Inductive Switching, t_c and t_{fi}
$I_C/I_B = 10$

TYPICAL SWITCHING CHARACTERISTICS
(I_{B2} = I_C/2 for all switching)
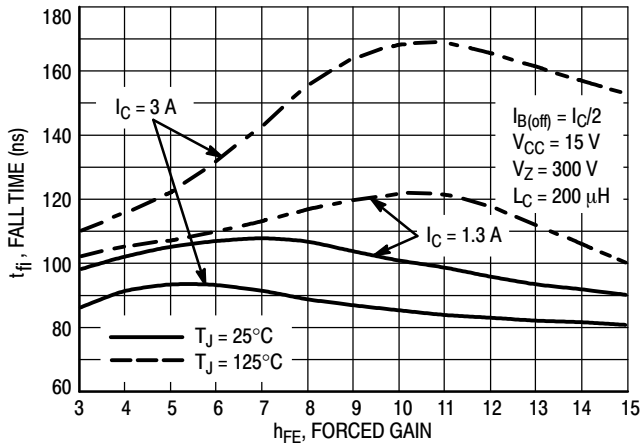
Figure 13. Inductive Fall Time
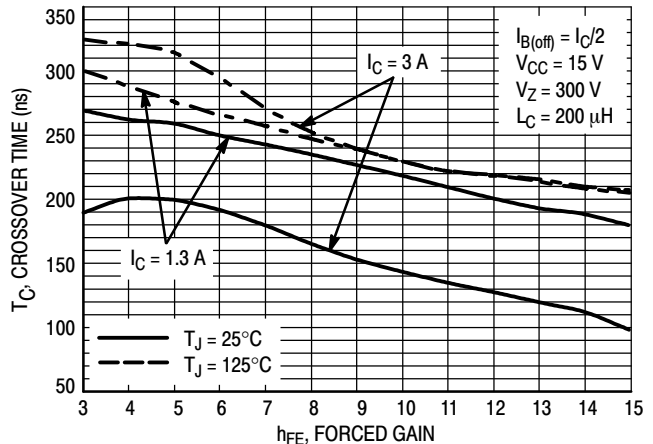
Figure 14. Inductive Crossover Time

GUARANTEED SAFE OPERATING AREA INFORMATION
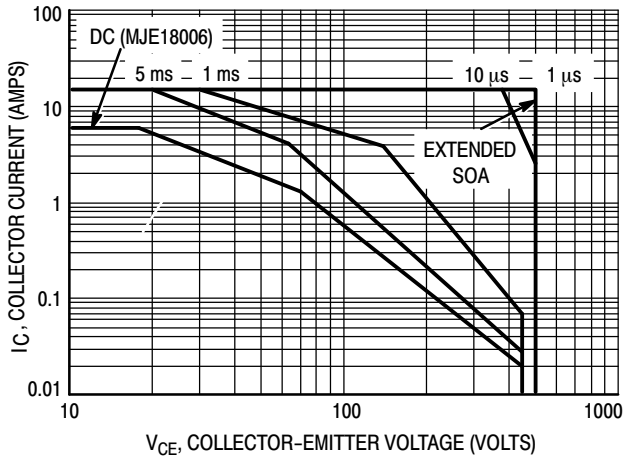
Figure 15. Forward Bias Safe Operating Area
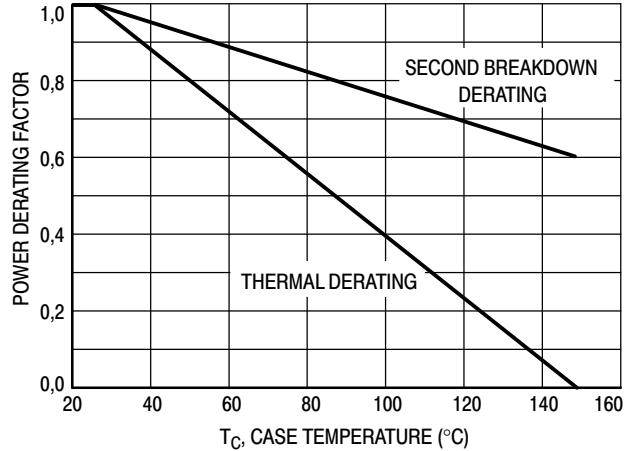
Figure 17. Forward Bias Power Derating
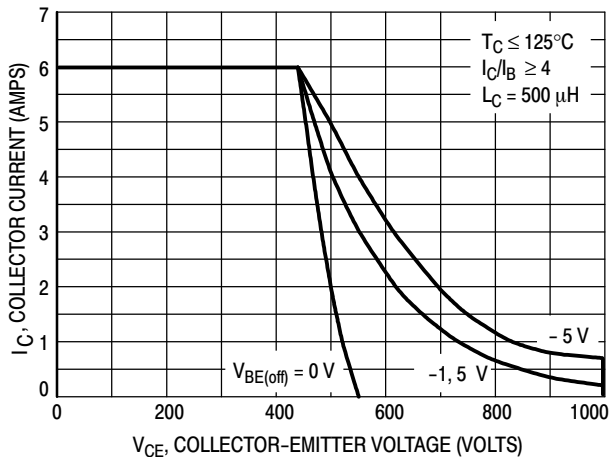
Figure 16. Reverse Bias Switching Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 15 is based on T_C = 25°C; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_C \geq 25$°C. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown in Figure 15 may be found at any case temperature by using the appropriate curve on Figure 17. $T_{J(pk)}$ may be calculated from the data in Figure 20. At any case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. For inductive loads, high voltage and current must be sustained simultaneously during turn–off with the base–to–emitter junction reverse–biased. The safe level is specified as a reverse–biased safe operating area (Figure 16). This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode.
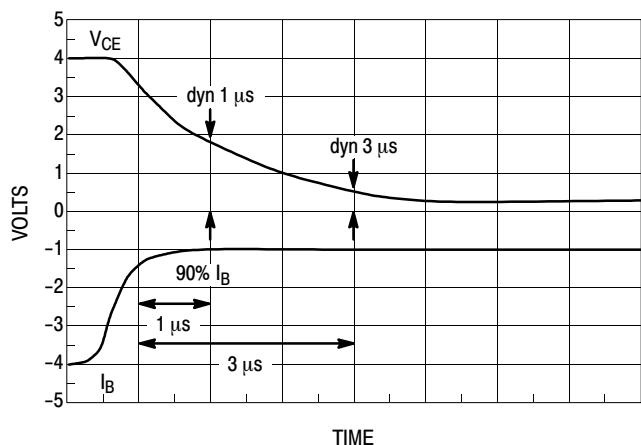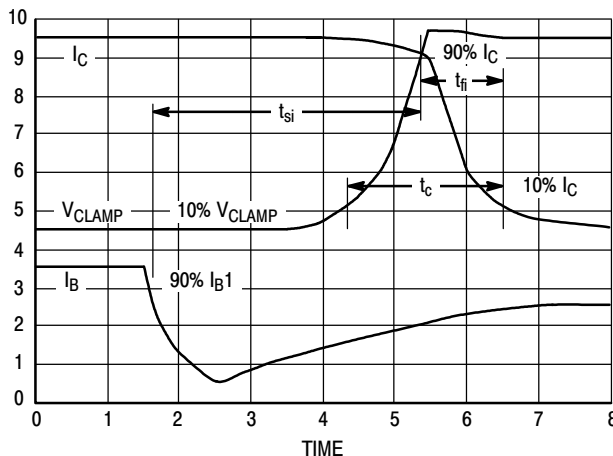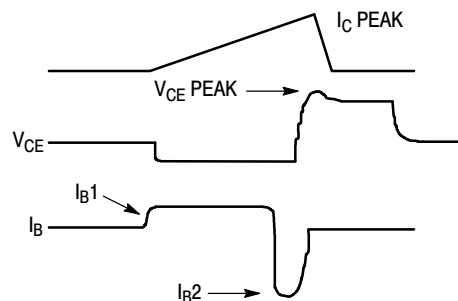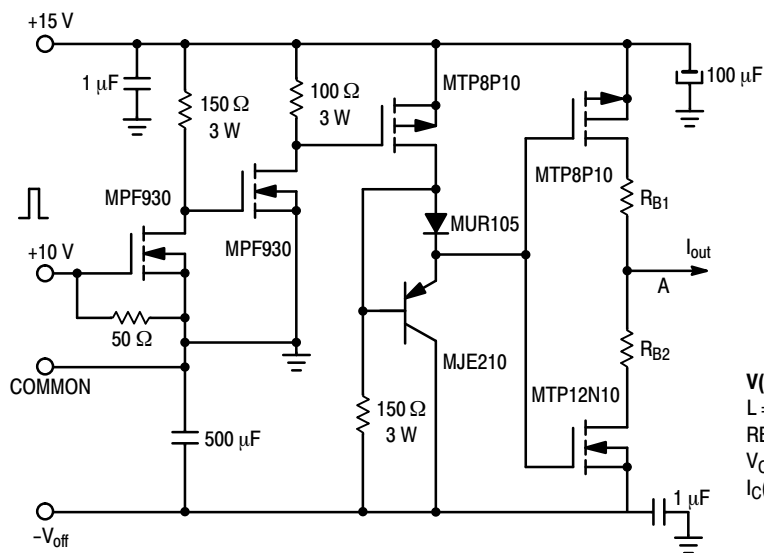
Figure 18. Dynamic Saturation Voltage Measurements

Figure 19. Inductive Switching Measurements

V(BR)CEO(sus)
L = 10 mH
RB2 = ∞
V_{CC} = 20 VOLTS
I_C(pk) = 100 mA

INDUCTIVE SWITCHING
L = 200 μH
RB2 = 0
V_{CC} = 15 VOLTS
RB1 SELECTED FOR
DESIRED I_{B1}

RBSOA
L = 500 μH
RB2 = 0
V_{CC} = 15 VOLTS
RB1 SELECTED
FOR DESIRED I_{B1}

Table 1. Inductive Load Switching Drive Circuit

TYPICAL THERMAL RESPONSE

$R_{\theta JC}(t) = r(t) R_{\theta JC}$
$R_{\theta JC}$ = 1.25°C/W MAX
D CURVES APPLY FOR POWER
PULSE TRAIN SHOWN
READ TIME AT t_1
$T_{J(pk)} - T_C = P_{(pk)} R_{\theta JC}(t)$

DUTY CYCLE, D = t_1/t_2
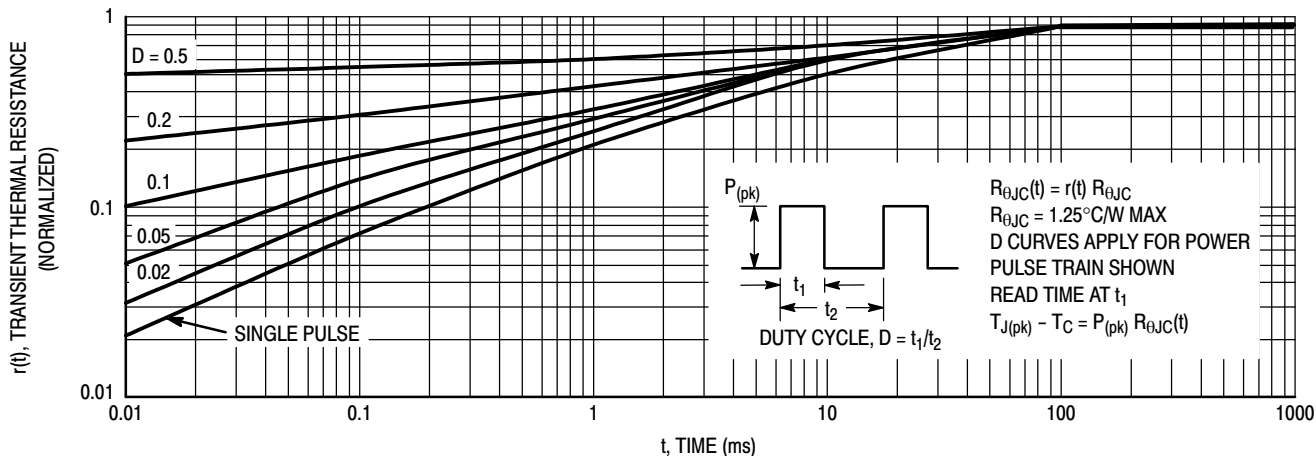
Figure 20. Typical Thermal Response ($Z_{\theta JC}(t)$) for MJE18006

PACKAGE DIMENSIONS

TO−220AB
CASE 221A−09
ISSUE AF
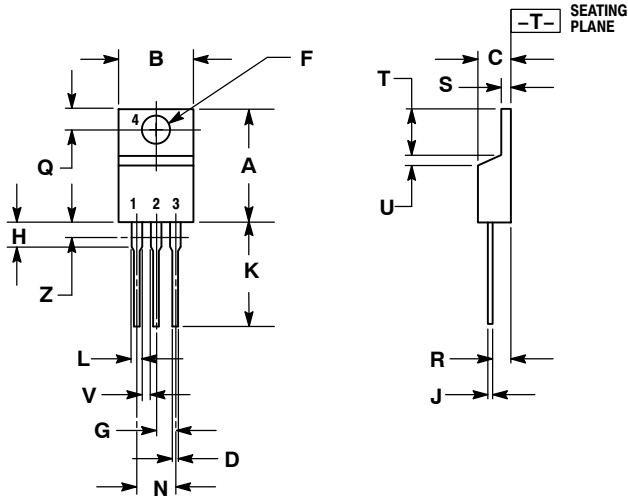
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

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